

25C D ■ 8235605 0004041 4 ■ SIEG

PNP Transistors for AF Input Stages

ACY 23
ACY 32

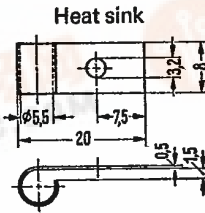
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SIEMENS AKTIENGESELLSCHAFT

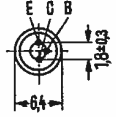
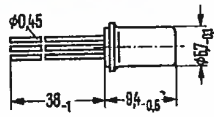
ACY 23 and ACY 32 are alloyed germanium PNP transistors in 1 A 3 DIN 41871 case (similar to TO-1). All leads are electrically insulated from the case. The collector terminal is marked by a red dot on the rim of the case. The transistors are particularly intended for use in AF input stages.

T-29-11

Type	Ordering code
ACY 23 V	Q60103-Y23-E
ACY 23 VI	Q60103-Y23-F
ACY 32 V	Q60103-Y32-E
ACY 32 VI	Q60103-Y32-F
Heat sink	Q62901-B1



Not for new design



Approx. weight 1 g

Dimensions in mm

Thermal resistance between transistor case and heat sink below the fixing screw at careful mounting: $R_{th} \leq 10 \text{ K/W}$

Maximum ratings	ACY 23, ACY 32	
Collector-emitter voltage	$-V_{CEO}$	30 V
Collector-emitter voltage ($V_{BE} \geq 0.2 \text{ V}$)	$-V_{CEV}$	32 V
Collector-base voltage	$-V_{CBO}$	32 V
Emitter-base voltage	$-V_{EBO}$	16 V
Collector current	$-I_C$	200 mA
Base current	$-I_B$	40 mA
Junction temperature	T_j	90 °C
Storage temperature range	T_{stg}	-55 to +75 °C
Total power dissipation ($T_{case} = 45 \text{ °C}$)	P_{tot}	900 mW
Thermal resistance		
Junction to ambient air	R_{thJA}	$\leq 300 \text{ K/W}$
Junction to case	R_{thJC}	$\leq 50 \text{ K/W}$



T-29-11

Static characteristics ($T_{amb} = 25^\circ\text{C}$)

ACY 23, ACY 32

	T_{amb}	25	60	$^\circ\text{C}$
Collector cutoff current ($-V_{CBO} = 10\text{ V}$)	$-I_{CBO}$	3 (<10)	60 (<100)	μA
Collector cutoff current ($-V_{CBO} = 32\text{ V}$)	$-I_{CBO}$	5 (<18)	<150	μA
Collector cutoff current ($-V_{CEV} = 32\text{ V}; V_{BE} \geq 0.2\text{ V}$)	$-I_{CEV}$	5 (<18)*	<150	μA
Emitter cutoff current ($-V_{EBO} = 16\text{ V}$)	$-I_{EBO}$	4 (<18)*	<120	μA

Static characteristics ($T_{amb} = 25^\circ\text{C}$) ACY 23, ACY 32

$-V_{CE}$	$-I_C$ mA	$-I_B$ μA	h_{FE} I_C/I_B	V_{BE} V
0.5	2	30	67	0.13 (<0.2)
0.5	10	137	73	0.18 (<0.3)
0.5	100	1560	64	0.32 (<0.55)

Collector-emitter saturation voltage ($I_C = 100\text{ mA}; I_B = 5\text{ mA}$)	$-V_{CEsat}$	0.11 (<0.18)	V
Collector-emitter saturation voltage ($-I_C = 200\text{ mA}$ for the characteristic which, at constant base current, intersects the operating point, where $-I_C = 220\text{ mA}$ and $-V_{CE} = 0.5\text{ V}$)	$-V_{CEsat}$	0.25 (<0.4)	V

Dynamic characteristics ($T_{amb} = 25^\circ\text{C}$)

The transistors ACY 23 and ACY 32 are grouped according to the small-signal current gain h_{fe} and marked by Roman numerals.

Operating point: $-I_C = 1\text{ mA}; -V_{CE} = 5\text{ V}; f = 1\text{ kHz}$

h_{fe} group	V	VI	
h_{fe}	50 to 100 ACY 23	75 to 150* ACY 32	-
Operating point: $-I_C = 1\text{ mA}; -V_{CE} = 5\text{ V}$			
Transition frequency f_T	1.5 (>0.5)	1.5 (>0.5)	MHz
Base intrinsic resistance $r_{bb'}$	75 (<200)	75 (<200)	Ω
Collector-junction capacitance $C_{b'c}$	27	27	pF
Noise figure ($-I_C = 0.5\text{ mA}; -V_{CE} = 5\text{ V}; f = 1\text{ kHz}; \Delta f = 200\text{ Hz}; R_g = 500\ \Omega$)	NF		dB
Operating point: $-I_C = 1\text{ mA}; -V_{CE} = 5\text{ V}; f = 1\text{ kHz}$			
h_{11e}	3 (1.2 to 5)	3 (1.2 to 5)	k Ω
h_{12e}	7 (<15)	7 (<15)	10^{-4}
h_{21e}	100 (50 to 150)	100 (50 to 150)	-
h_{22e}	40 (<75)	40 (<75)	μS

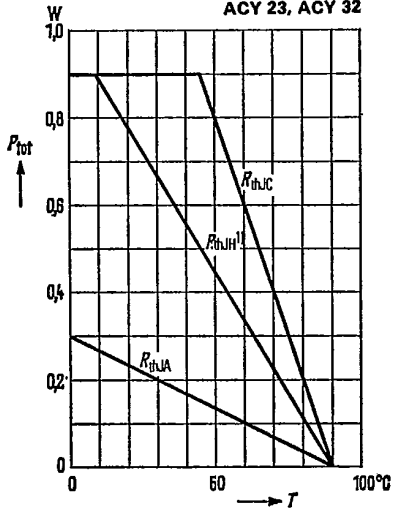
*AQL = 0.65%

T-29-11

Total perm. power dissipation versus temperature

$P_{tot} = f(T); R_{th} = \text{parameter}$

ACY 23, ACY 32



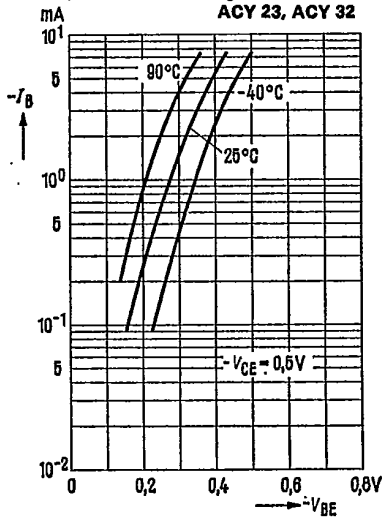
1) Heat sink aluminum 12.5 cm² x 2 mm

Input characteristics $I_B = f(V_{BE})$

$-V_{BE} = 0.5 \text{ V}; T_{amb} = \text{parameter}$

(common emitter configuration)

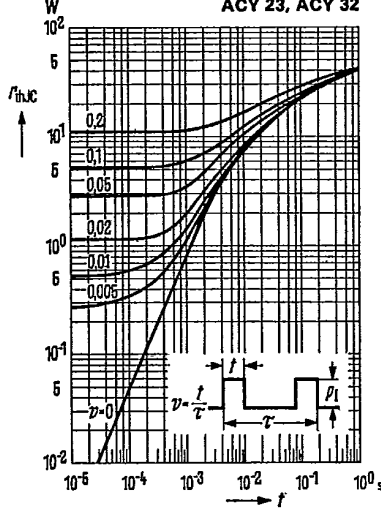
ACY 23, ACY 32



Permissible pulse load

$r_{thJC} = f(t); v = \text{parameter}$

ACY 23, ACY 32

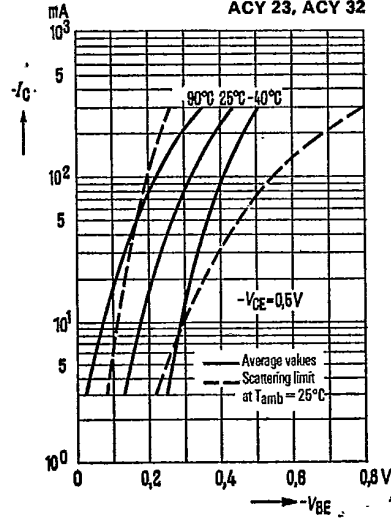


Collector current $I_C = f(V_{BE})$

$-V_{CE} = 0.5 \text{ V}; T_{amb} = \text{parameter}$

(common emitter configuration)

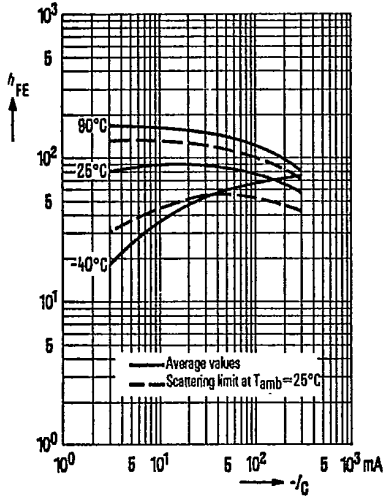
ACY 23, ACY 32



T-29-11

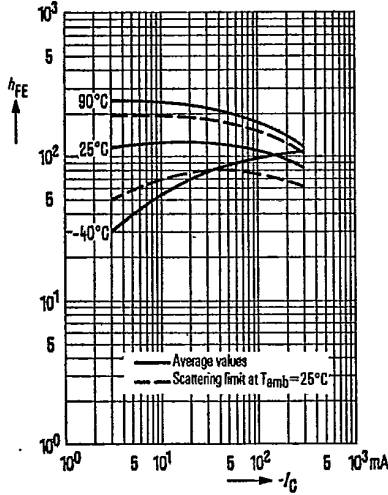
DC current gain $h_{FE} = f(I_C)$
 $-V_{CE} = 0.5 \text{ V}; T_{amb} = \text{parameter}$
 (common emitter configuration)

ACY 23 V, ACY 32 V



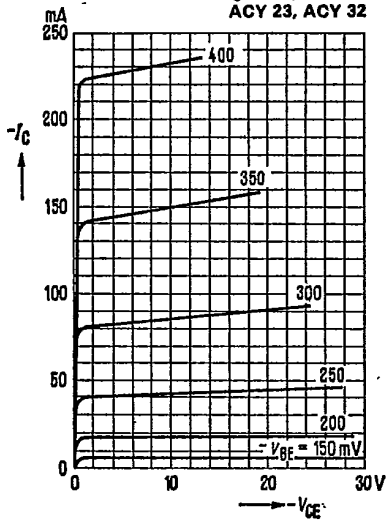
DC current gain $h_{FE} = f(I_C)$
 $-V_{CE} = 0.5 \text{ V}; T_{amb} = \text{parameter}$
 (common emitter configuration)

ACY 23 VI, ACY 32 VI



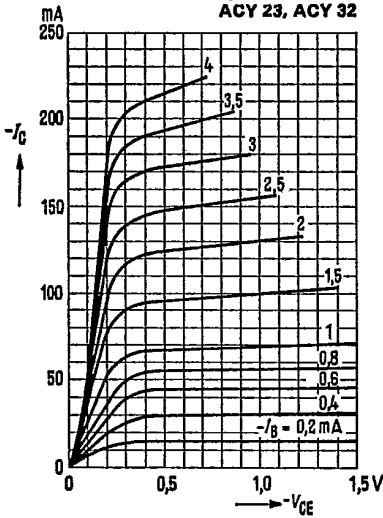
Output characteristics
 $I_C = f(V_{CE}); I_B = \text{parameter}$
 (common emitter configuration)

ACY 23, ACY 32



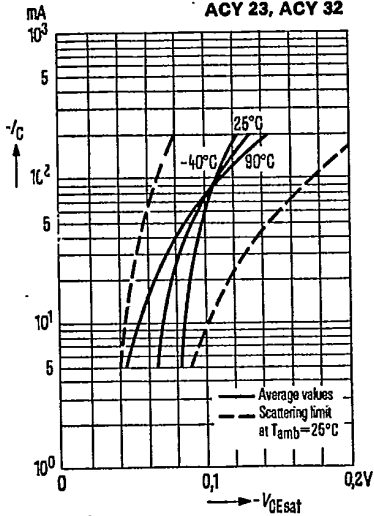
Output characteristics
 $I_C = f(V_{CE}); I_B = \text{parameter}$
 (common emitter configuration)

ACY 23, ACY 32

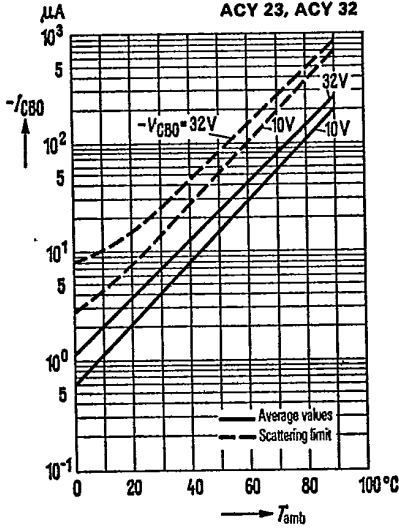


T-29-11

Collector-emitter saturation voltage
 $V_{CEsat} = f(I_C); h_{FE} = 20; T_{amb} = \text{parameter}$
 (common emitter configuration)
ACY 23, ACY 32



Collector cutoff current versus temperature
 $I_{CBO} = f(T_{amb})$
 $-V_{CBO} = 32\text{ V}; -V_{CBO} = 10\text{ V}$
ACY 23, ACY 32

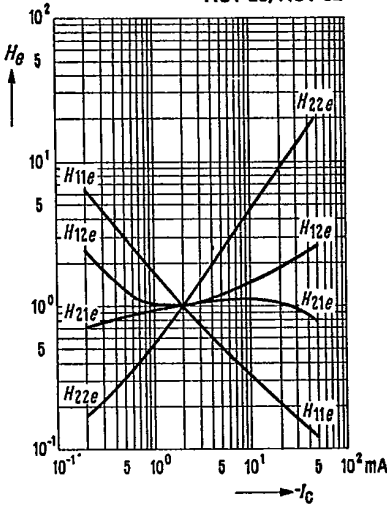


h-parameter versus collector current

$$H_o = \frac{h_o(I_C)}{h_o(I_C = -2\text{ mA})} = f(I_C)$$

$-V_{CE} = 1\text{ V}; f = 1\text{ kHz}$

ACY 23, ACY 32

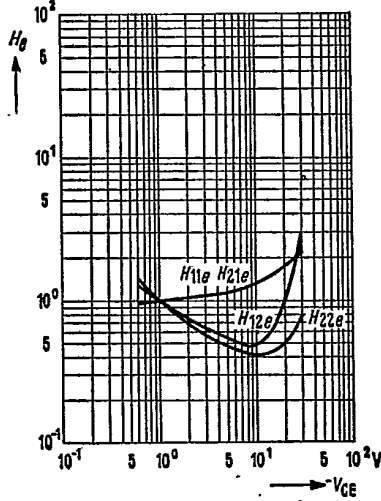


h-parameter versus collector-emitter voltage

$$H_o = \frac{h_o(V_{CE})}{h_o(V_{CE} = -1\text{ V})} = f(V_{CE})$$

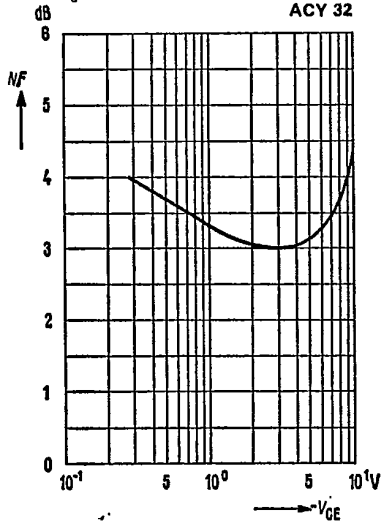
$-I_C = 2\text{ mA}; f = 1\text{ kHz}$

ACY 23, ACY 32

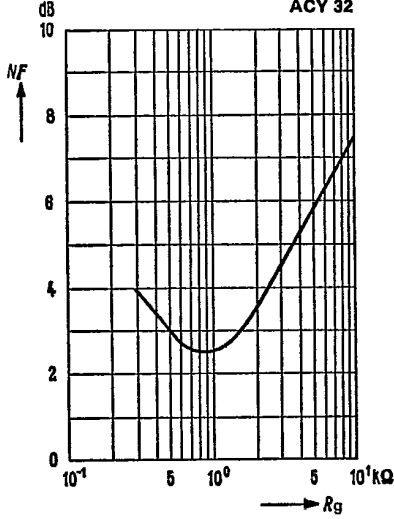


T-29-11

Noise figure versus collector-emitter voltage $NF = f(V_{CE})$
 $R_g = 500 \Omega$; $f = 1 \text{ kHz}$; $-I_C = 0.5 \text{ mA}$



Noise figure versus internal resistance of generator $NF = f(R_g)$
 $f = 1 \text{ kHz}$; $-I_C = 0.5 \text{ mA}$; $-V_{CE} = 5 \text{ V}$



Noise figure versus collector current $NF = f(I_C)$
 $R_g = 500 \Omega$; $-V_{CE} = 5 \text{ V}$; $f = 1 \text{ kHz}$

